

Switching Diodes Array

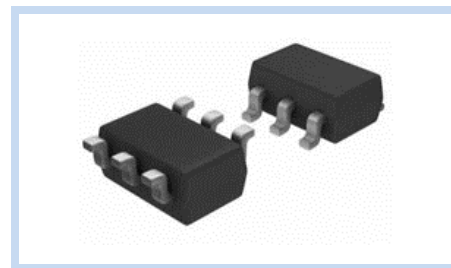
200mW SOT-363

BAW567DW

MERITEK

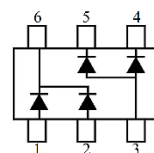
FEATURE

- Power Dissipation: 200mW
- Low Forward Voltage
- 150mA Average Rectified Output Current
- Fast Switching Speed



MECHANICAL DATA

- Case: SOT-363, Molded Plastic
- Terminals: Solderable per MIL-STD, Method 2026



MAXIMUM RATING

Parameter	Symbol	Value	Units
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	V_R	75	V
Average Forward Rectified Current	$I_{F(AV)}$	150	mA
Forward Continuous Current	I_{FM}	300	mA
Peak Forward Surge Current	I_{FSM}	$t = 1s$	1
		$t = 2\mu s$	2
Power Dissipation Derate above 25°C	P_D	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	°C / W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS

Parameter	Conditions	Symbol	Min	Max	Unit
Reverse Breakdown Voltage	$I_R = 10\mu A$	$V_{(BR)R}$	75	--	V
Instantaneous Forward Voltage	$I_F = 1mA$	V_F	--	0.715	V
	$I_F = 10mA$		--	0.855	
	$I_F = 50mA$		--	1.000	
	$I_F = 150mA$		--	1.250	
Reverse Leakage Current	$V_R = 20V$	I_R	--	25	nA
	$V_R = 75V$		--	2.5	μA
	$V_R = 25V, T_J = 150^\circ C$		--	30	
	$V_R = 75V, T_J = 150^\circ C$		--	50	
Capacitance	$V_R = 0V, f = 1MHz$	C_T	--	2	pF
Reverse Recovery Time	$I_F = 10mA, V_R = 75V, I_{rr} = 0.1I_R, R_L = 100\Omega$	t_{rr}	--	4	nS

Note:

1. $T_A = 25^\circ C$ unless otherwise specified.
2. Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.

Switching Diodes Array

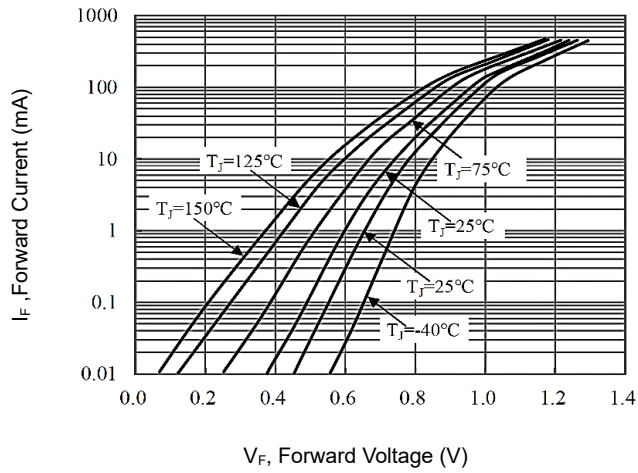
200mW SOT-363

BAW567DW

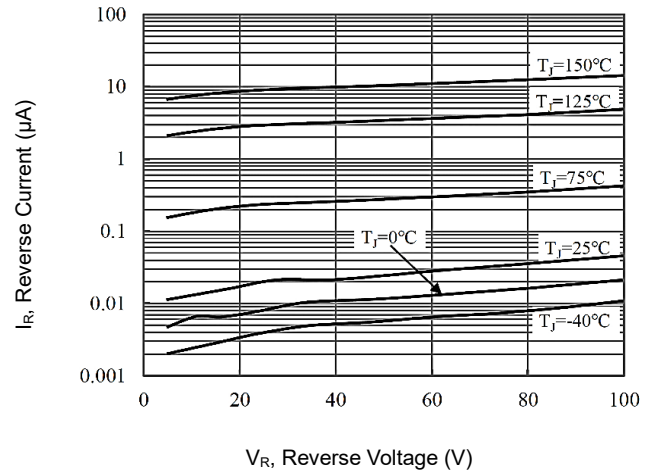
MERITEK

CHARACTERISTIC CURVES

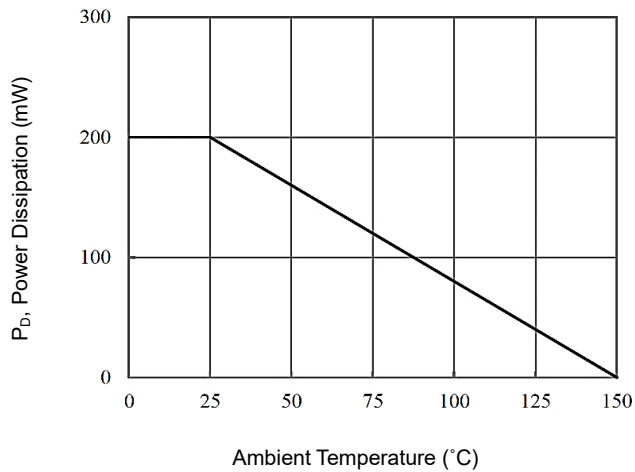
Typical Forward Characteristics



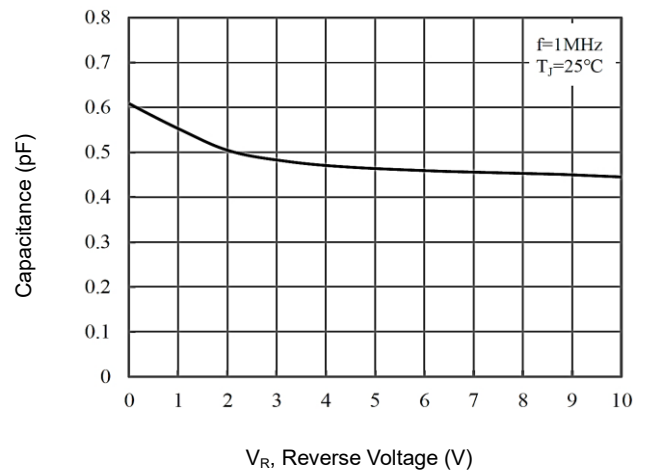
Typical Reverse Characteristics



Power Derating Curve



Capacitance



Switching Diodes Array

200mW SOT-363

BAW567DW

MERITEK

DIMENSIONS

SOT-363	Min (mm)	Max (mm)
A1	0.00	0.10
A2	0.90	1.00
A3	0.90	1.10
b	0.10	0.25
c	0.10	0.25
D	1.80	2.20
e	0.65	
e1	1.30	
E	2.00	2.20
E1	1.15	1.35
L	0.15	0.40
X	0.42	
X1	0.65	
Y	1.30	
Y1	0.60	
Y2	2.50	

